

First Named Inventor	Andrei Mihnea
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Filing Date	August 7, 2003
Group Art Unit	2801
Examiner Name	Unknown
Confirmation No.	1762
Attorney Docket No.	400.237USO
Title: METHOD FOR ERASING AN IMAGE	

Sheet 1 of 7

INFORMATION DISCLOSURE
STATEMENT
FORM PTO-1449

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Serial No.	10/636,181	
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Examiner Name	Unknown Ly D. Pham	
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Title: METHOD FOR ERASING AN NROM CELL		Sheet 3 of 7

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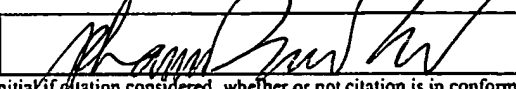
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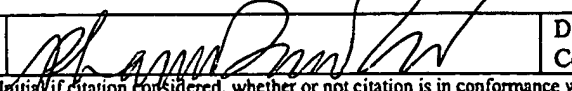
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